2-Input NAND Schmitt-Trigger

The MC74VHC1G132 is a single gate CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G132 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1G132 to be used to interface 5 V circuits to 3 V circuits.

The MC74VHC1G132 can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- High Speed: $t_{PD} = 3.6 \text{ ns} (Typ) \text{ at } V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1.0 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 68; Equivalent Gates = 16
- Pb–Free Packages are Available

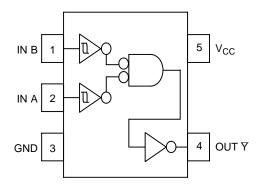


Figure 1. Pinout (Top View)

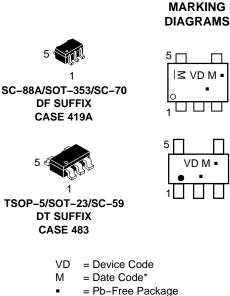


Figure 2. Logic Symbol



ON Semiconductor®

http://onsemi.com



= PD-Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT						
IN B						
IN A						
GND						
Ουτ γ						
V _{CC}						

FUNCTION TABLE

Inp	uts	Output
Α	В	Ŧ
L	L	Н
L	Н	Н
н	L	Н
Н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

© Semiconductor Components Industries, LLC, 2007 February, 2007 – Rev. 18

MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V	
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to V_{CC} $+0.5$	V
I _{IK}	DC Input Diode Current		-20	mA
I _{OK}	DC Output Diode Current		±20	mA
I _{OUT}	DC Output Sink Current		± 12.5	mA
I _{CC}	DC Supply Current per Supply Pin	±25	mA	
T _{STG}	Storage Temperature Range	-65 to +150	°C	
ΤL	Lead Temperature, 1 mm from Case	e for 10 Seconds	260	°C
ΤJ	Junction Temperature Under Bias		+ 150	°C
θ_{JA}	Thermal Resistance	SC70–5/SC–88A (Note 1) TSOP–5	350 230	°C/W
PD	Power Dissipation in Still Air at 85°C	SC70–5/SC–88A TSOP–5	150 200	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I _{LATCHUP}	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 5)	± 500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage		0.0	5.5	V
V _{OUT}	DC Output Voltage		0.0	V _{CC}	V
T _A	Operating Temperature Range		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $\begin{array}{c} V_{CC}=3.3~V\pm\\ V_{CC}=5.0~V\pm \end{array}$	0.3 V 0.5 V	-	No Limit No Limit	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

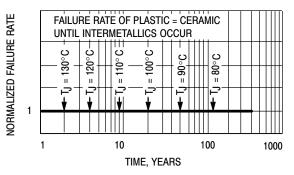


Figure 3. Failure Rate vs. Time Junction Temperature

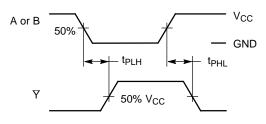
			v _{cc}		A = 25°	С	T _A ≤	85°C	$-55 \le T_A$	≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage		3.0 4.5 5.5	1.50 2.35 2.80	1.88 2.66 3.21	2.25 3.10 3.70	1.50 2.35 2.80	2.25 3.10 3.70	1.50 2.35 2.80	2.25 3.10 3.70	V
V _{T-}	Negative Threshold Voltage		3.0 4.5 5.5	0.65 1.10 1.45	1.03 1.62 2.02	1.40 2.10 2.60	0.65 1.10 1.45	1.40 2.10 2.60	0.65 1.10 1.45	1.40 2.10 2.60	V
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.85 1.05 1.20	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	V
V _{OH}	Minimum High-Level	$V_{IN} = V_{CC} \text{ or } GND$	2.0	1.9	2.0		1.9		1.9		V
	Output Voltage I _{OH} = −50μA	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu\text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.5		
		$I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μA

DC ELECTRICAL CHARACTERISTICS

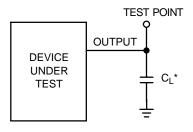
AC ELECTRICAL CHARACTERISTICS $C_{load} = 50 \text{ pF}$, Input $t_r/t_f = 3.0 \text{ ns}$

			T _A = 25°C		T _A ≤	85°C	-55 ≤ T _A	≤ 125°C			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Мах	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A or B to \overline{Y}	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.6 6.1	11.9 15.4	1.0 1.0	14.0 17.5	1.0 1.0	16.1 19.6	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		3.6 4.3	7.7 9.7	1.0 1.0	9.0 11.0	1.0 1.0	10.3 12.3	
C _{IN}	Maximum Input Capaci- tance				5.5	10		10		10	pF
					1	Typical	@ 25°C	, V _{CC} =	5.0 V		
C _{PD}	Power Dissipation Capacit	ance (Note 6)					11				pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.







*Includes all probe and jig capacitance

Figure 5. Test Circuit

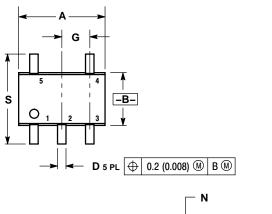
ORDERING INFORMATION

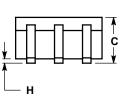
Device	Package	Shipping [†]
MC74VHC1G132DFT1	SC70-5/SC-88A/SOT-353	
M74VHC1G132DFT1G	SC70-5/SC-88A/SOT-353 (Pb-Free)	
MC74VHC1G132DFT2	SC70-5/SC-88A/SOT-353	
M74VHC1G132DFT2G	SC70–5/SC–88A/SOT–353 (Pb–Free)	3000 Units / Tape & Reel
MC74VHC1G132DTT1	SOT23-5/TSOP-5SC59-5	
M74VHC1G132DTT1G	SOT23–5/TSOP–5SC59–5 (Pb–Free)	

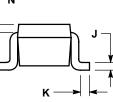
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70 CASE 419A-02 ISSUE J



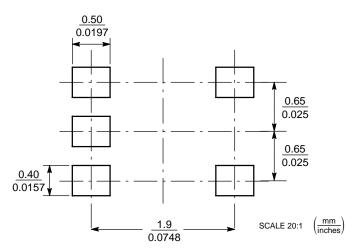


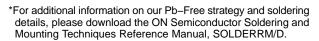


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

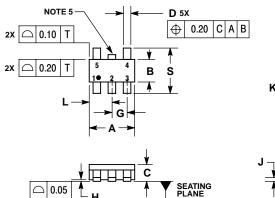
SOLDERING FOOTPRINT*





PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 **ISSUE F**



T



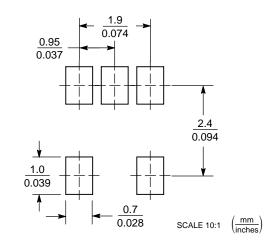


NOTES

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD 2 3. THICKNESS IS THE MINIMUM THICKNESS
- OF BASE MATERIAL. DIMENSIONS A AND B DO NOT INCLUDE 4 MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED 5 IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS						
DIM	MIN MAX						
Α	3.00	BSC					
В	1.50	BSC					
С	0.90 1.10						
D	0.25 0.50						
G	0.95 BSC						
н	0.01	0.10					
J	0.10	0.26					
к	0.20	0.60					
L	1.25 1.55						
м	0° 10°						
S	2.50	3.00					

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative